

Vladimir Protasenko

List of Publications by Year in Descending Order

Source: <https://exaly.com/author-pdf/6448182/vladimir-protasenko-publications-by-year.pdf>

Version: 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

29
papers

1,430
citations

17
h-index

33
g-index

33
ext. papers

1,632
ext. citations

4.3
avg, IF

4.18
L-index

#	Paper	IF	Citations
29	MBE growth and donor doping of coherent ultrawide bandgap AlGaIn alloy layers on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2021 , 118, 092101	3.4	5
28	Phase inclusions as common structural defects in alloyed $\text{Al}_{1-x}\text{Ga}_x\text{In}_x\text{N}$ and doped AlGaInN films. <i>APL Materials</i> , 2021 , 9, 051119	5.7	7
27	Crystal orientation dictated epitaxy of ultrawide-bandgap 5.4- to 8.6-eV AlGaInN on m-plane sapphire. <i>Science Advances</i> , 2021 , 7,	14.3	35
26	Fighting Broken Symmetry with Doping: Toward Polar Resonant Tunneling Diodes with Symmetric Characteristics. <i>Physical Review Applied</i> , 2020 , 13,	4.3	8
25	Bottom tunnel junction blue light-emitting field-effect transistors. <i>Applied Physics Letters</i> , 2020 , 117, 031107	3.4	2
24	Light-emitting diodes with AlN polarization-induced buried tunnel junctions: A second look. <i>Applied Physics Letters</i> , 2020 , 117, 061104	3.4	5
23	Bandgap narrowing and Mott transition in Si-doped $\text{Al}_{0.7}\text{Ga}_{0.3}\text{N}$. <i>Applied Physics Letters</i> , 2019 , 114, 113501	3.4	6
22	Broken Symmetry Effects due to Polarization on Resonant Tunneling Transport in Double-Barrier Nitride Heterostructures. <i>Physical Review Applied</i> , 2019 , 11,	4.3	17
21	Efficient InGaIn p-Contacts for deep-UV Light Emitting Diodes 2019 ,		2
20	Room temperature microwave oscillations in GaN/AlN resonant tunneling diodes with peak current densities up to 220 kA/cm ² . <i>Applied Physics Letters</i> , 2018 , 112, 103101	3.4	38
19	MBE-grown 232-70 nm deep-UV LEDs using monolayer thin binary GaN/AlN quantum heterostructures. <i>Applied Physics Letters</i> , 2017 , 110, 041108	3.4	85
18	New Tunneling Features in Polar III-Nitride Resonant Tunneling Diodes. <i>Physical Review X</i> , 2017 , 7,	9.1	34
17	Deep-UV emission at 219 nm from ultrathin MBE GaN/AlN quantum heterostructures. <i>Applied Physics Letters</i> , 2017 , 111, 091104	3.4	42
16	Extended Defect Propagation in Highly Tensile-Strained Ge Waveguides. <i>Crystals</i> , 2017 , 7, 157	2.3	2
15	Layered transition metal dichalcogenides: promising near-lattice-matched substrates for GaN growth. <i>Scientific Reports</i> , 2016 , 6, 23708	4.9	58
14	Deep ultraviolet emission from ultra-thin GaN/AlN heterostructures. <i>Applied Physics Letters</i> , 2016 , 109, 241102	3.4	53
13	Self-assembled Ge QDs Formed by High-Temperature Annealing on Al(Ga)As (001). <i>Journal of Electronic Materials</i> , 2015 , 44, 1338-1343	1.9	2

12	Esaki Diodes in van der Waals Heterojunctions with Broken-Gap Energy Band Alignment. <i>Nano Letters</i> , 2015 , 15, 5791-8	11.5	237
11	Deep-UV LEDs using polarization-induced doping: Electroluminescence at cryogenic temperatures 2015 ,		1
10	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. <i>Applied Physics Letters</i> , 2014 , 104, 193506	3-4	35
9	Tunnel-injection quantum dot deep-ultraviolet light-emitting diodes with polarization-induced doping in III-nitride heterostructures. <i>Applied Physics Letters</i> , 2014 , 104, 021105	3-4	68
8	High-voltage field effect transistors with wide-bandgap EGa_2O_3 nanomembranes. <i>Applied Physics Letters</i> , 2014 , 104, 203111	3-4	242
7	Tunnel-injection GaN quantum dot ultraviolet light-emitting diodes. <i>Applied Physics Letters</i> , 2013 , 102, 041103	3-4	56
6	Nanomembrane EGa_2O_3 high-voltage field effect transistors 2013 ,		1
5	First demonstration of two-dimensional WS_2 transistors exhibiting 105 room temperature modulation and ambipolar behavior 2012 ,		2
4	Transistors with chemically synthesized layered semiconductor WS_2 exhibiting 105 room temperature modulation and ambipolar behavior. <i>Applied Physics Letters</i> , 2012 , 101, 013107	3-4	212
3	Polarization-engineering in group III-nitride heterostructures: New opportunities for device design. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 1511-1516	1.6	66
2	N-polar III-nitride quantum well light-emitting diodes with polarization-induced doping. <i>Applied Physics Letters</i> , 2011 , 99, 171104	3-4	55
1	CdSe nanowires with illumination-enhanced conductivity: Induced dipoles, dielectrophoretic assembly, and field-sensitive emission. <i>Journal of Applied Physics</i> , 2007 , 101, 073704	2.5	48